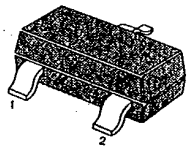
KSR1108 NPN EPITAXIAL SILICON TRANSISTOR

SWITCHING APPLICATION (Bias Resistor Built In)

- Switching Circuit, Inverter, Interface circuit Driver circuit
- Built In bias Resistor (R_1=47KΩ, R_2=22KΩ)
- Complement to KSR2108

SOT-23



1. Base 2. Emitter 3. Collector

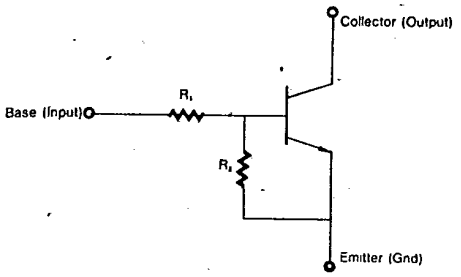
ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	10	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	200	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	−55~150	°C

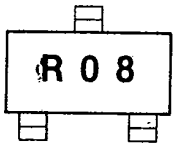
ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=10μA, I_E=0	50			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=100μA, I_B=0	50			V
Collector Cutoff Current	I_{CBO}	V_{CB}=40V, I_E=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=5mA	56			
Collector-Emitter Saturation Voltage	V_{CE}(sat)	I_C=10mA, I_B=0.5mA			0.3	V
Current Gain-Bandwidth Product	f_T	V_{CE}=5mA, I_C=10V		250		MHz
Output Capacitance	Cob	V_{CB}=10V, I_E=0 f=1.0MHz		3.7		pF
Input Off Voltage	Vi(off)	V_{CE}=5V, I_C=100μA	0.8			V
Input On Voltage	Vi(on)	V_{CE}=0.3V, I_C=2mA			4	V
Input Resistor	R_1		32	47	62	KΩ
Resistor Ratio	R_1/R_2		1.9	2.1	2.4	

Equivalent Circuit



Marking



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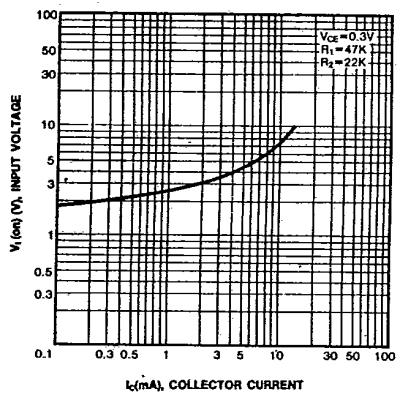
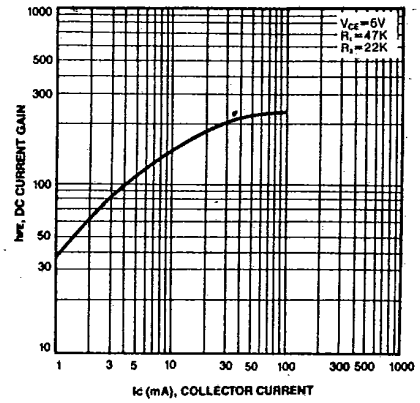
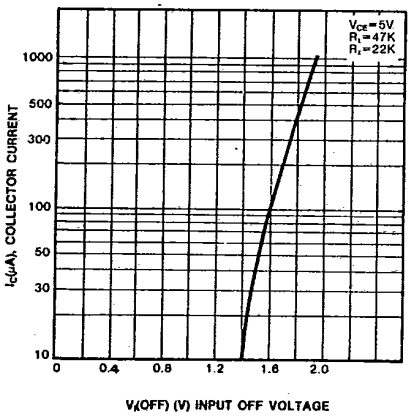
INPUT ON VOLTAGE



DC CURRENT GAIN



INPUT OFF VOLTAGE



POWER DERATING